## NPN High Voltage Transistor

The MMBT5551M3 device is a spin-off of our popular SOT-23 three-leaded device. It is designed for general purpose high voltage applications and is housed in the SOT-723 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

#### **Features**

- Reduces Board Space
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	160	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	180	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current – Continuous	Ic	60	mAdc

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	265 2.1	mW mW/°C
Thermal Resistance, Junction–to–Ambient (Note 1)	$R_{\theta JA}$	470	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	640 5.1	mW mW/°C
Thermal Resistance, Junction–to–Ambient (Note 2)	$R_{\theta JA}$	195	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

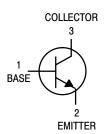
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.



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# 3

## SOT-723 CASE 631AA STYLE 1



**MARKING** 

АН

Specific Device CodeDate Code

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MMBT5551M3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSVMMBT5551M3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (Note 3) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	V <sub>(BR)CEO</sub>	160	_	Vdc
Collector – Base Breakdown Voltage $(I_C = 100 \mu Adc, I_E = 0)$	V <sub>(BR)CBO</sub>	180	_	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10 \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	6.0	_	Vdc
Collector Cutoff Current $(V_{CB} = 120 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 120 \text{ Vdc}, I_E = 0, T_A = 100^{\circ}\text{C})$	Ісво	- -	100 100	nAdc μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 4.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	50	nAdc
ON CHARACTERISTICS				
DC Current Gain $ \begin{aligned} &(I_C=1.0 \text{ mAdc}, V_{CE}=5.0 \text{ Vdc}) \\ &(I_C=10 \text{ mAdc}, V_{CE}=5.0 \text{ Vdc}) \\ &(I_C=50 \text{ mAdc}, V_{CE}=5.0 \text{ Vdc}) \end{aligned} $	h <sub>FE</sub>	80 80 30	_ 250 _	-
Collector – Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )	V <sub>CE(sat)</sub>	_ _	0.15 0.20	Vdc
Base – Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )	V <sub>BE(sat)</sub>	- -	1.0 1.0	Vdc
Collector Emitter Cut-off (V <sub>CB</sub> = 10 V) (V <sub>CB</sub> = 75 V)	ICES	_ _	50 100	nA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width = 300 µs, Duty Cycle = 2.0%.

## **TYPICAL CHARACTERISTICS**

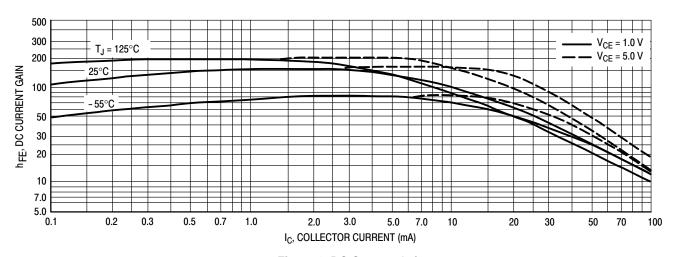


Figure 1. DC Current Gain

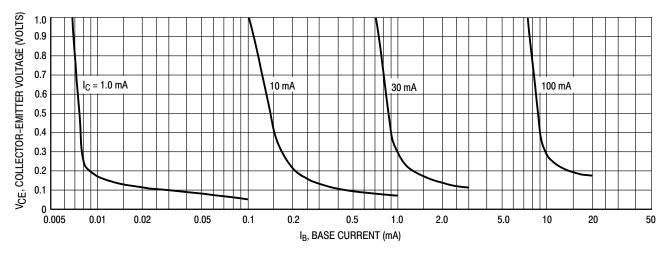


Figure 2. Collector Saturation Region

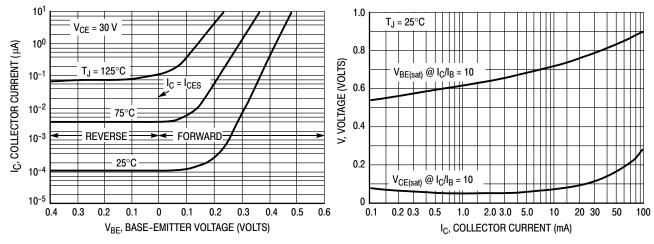
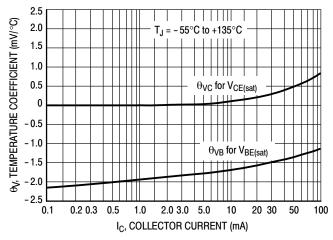


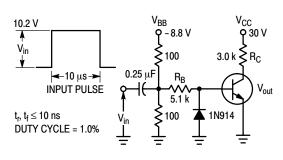
Figure 3. Collector Cut-Off Region

Figure 4. "On" Voltages

#### TYPICAL CHARACTERISTICS



**Figure 5. Temperature Coefficients** 



Values Shown are for I<sub>C</sub> @ 10 mA

Figure 6. Switching Time Test Circuit

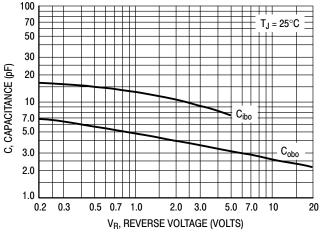


Figure 7. Capacitances

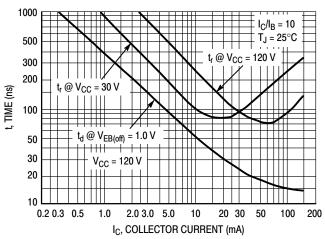


Figure 8. Turn-On Time

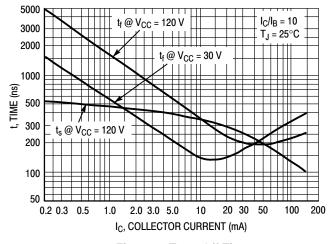


Figure 9. Turn-Off Time

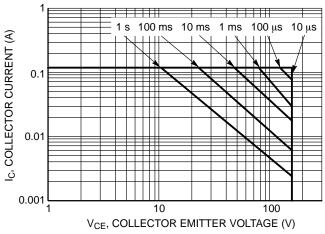


Figure 10. Safe Operating Area



SOT-723 CASE 631AA-01 ISSUE D

**DATE 10 AUG 2009** 

## NOTES:

- NOTES.

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
С	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
е	0.40 BSC		
ΗE	1.15	1.20	1.25
L	0.29 REF		
12	0.15	0.20	0.25

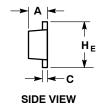
## **L2** 0.15 0.20 0.25 **GENERIC** MARKING DIAGRAM\*

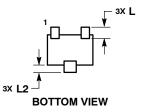


= Specific Device Code XX Μ = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

## -X-2X b ⊕ 0.08 X Y **TOP VIEW**

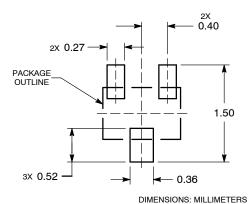




STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

**RECOMMENDED SOLDERING FOOTPRINT\*** 



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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